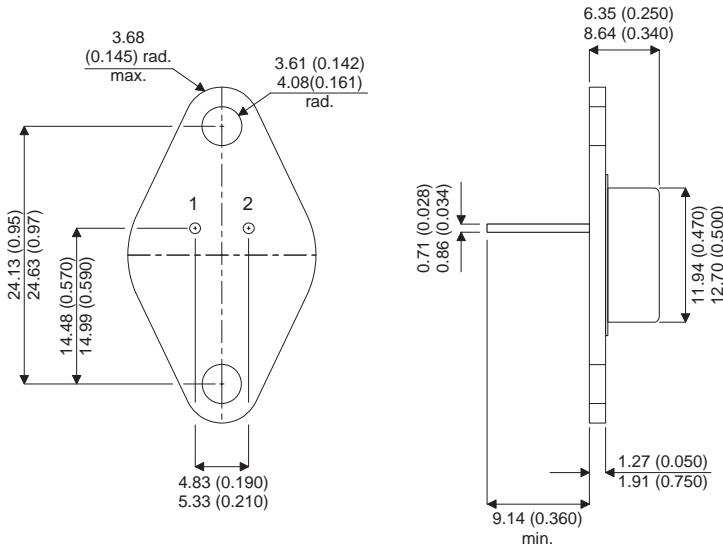


## NPN POWER SILICON TRANSISTOR IN A HERMETICALLY SEALED METAL PACKAGE

**MECHANICAL DATA**  
Dimensions in mm (inches)



**TO-66 (TO-213AA)**

**Underside View**

PIN 1 – Base      PIN 2 – Emitter      PIN 3 – Collector

**FEATURES**

- $V_{CEO} = 75V$
- $I_C = 7A$

**APPLICATIONS:**

All Semelab hermetically sealed products can be processed in accordance with the requirements of BS, CECC and JAN, JANTX, JANTXV and JANS specifications

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CEO}$	Collector-Emitter Voltage ( $I_B=0$ )	75V
$V_{CBO}$	Collector -Base Voltage ( $I_E=0$ )	120V
$V_{EBO}$	Emitter-Base Voltage ( $I_C=0$ )	7V
$I_B$	Continuous Base Current	5A
$I_C$	Continuous Collector Current	7A
$P_D$	Power Dissipation	$T_{case} = 25^{\circ}C$ 35W
$T_j, T_{stg}$	Operating & Storage Temperature Range	-65 to +200°C
$R_{JC}$	Thermal Resistance Junction to Case	5°C/W

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CEO}^*$ Collector-Emitter Breakdown Voltage	$I_C=0.2A$	75			V
$I_{CEO}^*$ Collector-Emitter Cut-Off Current	$V_{CE}=50V$			5.0	V
$I_{CEX}^*$ Collector-Emitter Cut-Off Current	$V_{CE}=100V$ $V_{BE}=1.5V$			4.0	mA
$I_{CBO}^*$ Collector-Base Cut-Off Current	$V_{CB}=120V$			25	
$I_{EBO}^*$ Emitter-Base Cut-Off Current	$V_{EB}=7V$			10	
$h_{FE}^*$ DC Current Gain	$I_C=0.5A$ $V_{CE}=5V$	40			—
	$I_C=4A$ $V_{CE}=5V$	20		80	
	$I_C=4A$ $V_{CE}=2V$	12		100	
$V_{CE(sat)}^*$ Collector-Emitter Saturation Voltage	$I_C=4A$ $I_B=0.4A$			1.2	V
$V_{BE(sat)}^*$ Base-Emitter Saturation Voltage	$I_C=4A$ $I_B=0.4A$			2.0	
$V_{BE(on)}^*$ Base-Emitter Saturation Voltage	$I_C=4A$ $V_{CE}=2V$			1.8	

\* Pulse Width < 300 $\mu$ s, Duty Cycle <2%

**DYNAMIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$ h_{fe} $ Small Signal Current Gain (f=10MHz)	$I_C=0.5A$ $V_{CE}=10V$	4	20		—
$C_{obo}$ Output Capacitance (0.1 ` f ` 1MHz)	$I_E=0A$ $V_{CB}=10V$			175	pF

**SWITCHING CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{on}$ Turn On Time	$I_C=0.2A$ $V_{CC}=30V$			0.44	$\mu$ s
	$I_B=0.4A$				
$t_{off}$ Turn Off Time	$I_C=0.2A$ $V_{CC}=30V$			1.22	
	$I_B=-I_B=0.4A$				

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